

PNP General Purpose Transistor

SST6839

●Features

- 1) $BV_{CEO} < -40V$ ($I_c = -1mA$)
- 2) Complements the SST6838.

●Package, marking, and packaging specifications

Part No.	SST6839
Packaging type	SST3
Marking	RFQ
Code	T116
Basic ordering unit (pieces)	3000

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_c	-0.2	A
Collector power dissipation	P_C	0.2	W
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

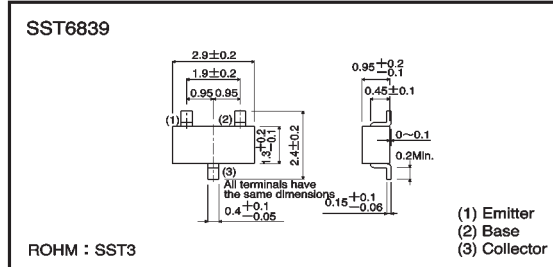
●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-50	—	—	V	$I_c = -10 \mu A$ (Ta=-40°C~+125°C)
Collector-emitter breakdown voltage	BV_{CEO}	-40	—	—	V	$I_c = -1mA$ (Ta=-40°C~+125°C)
Collector cutoff current	I_{CBO}	—	—	-0.5	μA	$V_{CB} = -30V$ (Ta=85°C)
		—	—	-5		$V_{CB} = -30V$ (Ta=125°C)
Emitter cutoff current	I_{EBO}	—	—	-0.5	μA	$V_{EB} = -4V$ (Ta=85°C)
		—	—	-5		$V_{EB} = -4V$ (Ta=125°C)
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.5	V	$I_c/I_b = -100mA/-10mA$ (Ta=85°C)
		—	—	-0.7		$I_c/I_b = -100mA/-10mA$ (Ta=125°C)
DC current transfer ratio	h_{FE1}	100	—	—	—	$V_{CE}/I_c = -5V/-1mA$ (Ta=-40°C~+25°C)
		—	—	800		$V_{CE}/I_c = -5V/-1mA$ (Ta=85°C)
		—	—	1000		$V_{CE}/I_c = -5V/-1mA$ (Ta=125°C)
DC current transfer ratio	h_{FE2}	100	—	—	—	$V_{CE}/I_c = -5V/-100mA$ (Ta=-40°C~+25°C)
Transition frequency	f_T	—	140	—	MHz	$V_{CE} = -12V, I_c = -2mA, f = 100MHz$ (Ta=25°C)
Collector output capacitance	C_{ob}	—	3.5	—	pF	$V_{CE} = -12V, I_e = 0A, f = 1MHz$ (Ta=25°C)
Emitter input capacitance	C_{ib}	—	17	—	pF	$V_{EB} = -0.5V, I_c = 0A, f = 1MHz$ (Ta=25°C)

●Electrical characteristic curves

The electrical characteristic curves for these products are the same as those of BC858BW and BC858B.
Refer to pages 603 to 606.

●External dimensions (Units : mm)



- (1) Emitter
- (2) Base
- (3) Collector